

ABSTRACT

Disclosed is a semiconductor memory device. In the process for the memory cell to reading stored data by selecting specific word lines, word lines
5 neighboring the selected word line are selected at the same time, or the two bit lines are connected at the same time to the input terminals of the sense amplifiers, thus increasing the difference in voltage between both the input terminals of the sense amplifiers. Therefore, the read margin is increased, the exactness of the read operation is increased, and reliability of the device is
10 improved.